



**PATENT APPLICATION**

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re application of

Docket No: Q61741

Takashi UDAGAWA

Appln. No.: 09/881,782

Group Art Unit: 2815

Confirmation No.: 1610

Examiner: Paul E. Brock II

Filed: June 18, 2001

RECEIVED  
JUN 24 2002  
TECHNOLOGY CENTER 2800

For: GROUP-III NITRIDE SEMICONDUCTOR LIGHT-EMITTING DIODE, LIGHT EMITTING DIODE LAMP, LIGHT SOURCE, ELECTRODE FOR GROUP-III NITRIDE SEMICONDUCTOR LIGHT-EMITTING DIODE, AND METHOD FOR PRODUCING THE ELECTRODE

**AMENDMENT UNDER 37 C.F.R. § 1.111**

Commissioner for Patents  
Washington, D.C. 20231

Sir:

In response to the Office Action dated March 14, 2002, kindly amend the above-identified application as follows:

**IN THE CLAIMS:**

**Please enter the following amended claims:**

1. (Amended) A group-III nitride semiconductor light-emitting diode comprising at least a first conduction-type single crystal substrate provided with a first conduction-type back-surface ohmic electrode on a back surface thereof, a buffer layer comprising a boron phosphide (BP)-based material on a front surface of said single crystal substrate, a gallium nitride (GaN)-based group-III nitride crystal layer having a light-emitting part of hetero-junction structure on said buffer layer, and a window layer comprising an electrically conducting transparent oxide

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03 FC:103 36.00 CH